

Applicant : Lin et al.  
Serial No. : 10/090,542  
Filed : March 4, 2002  
Page : 2 of 7

Attorney Docket: 13965-002001 / 0389-7381US

Amendments to the Specification:

Please replace the paragraph beginning at page 5, line 7 with the following amended paragraph:

As shown in FIG. 7, the dielectric layer 111 is patterned with photoresist 115, then anisotropically reactive ion etching (RIE) is employed to etch the dielectric layer 111 to form a opening an opening 116, then a P+ doping with boron is performed in the predetermined P+ doping region 109 (as shown in FIG. 5) such that a P+ doped region 117 is formed. Dosage of the doping is between  $10^{15}$  and  $1 \times 10^{16}$  atoms/cm<sup>2</sup>. Energy of the doping is between 1 and 3 keV.